

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

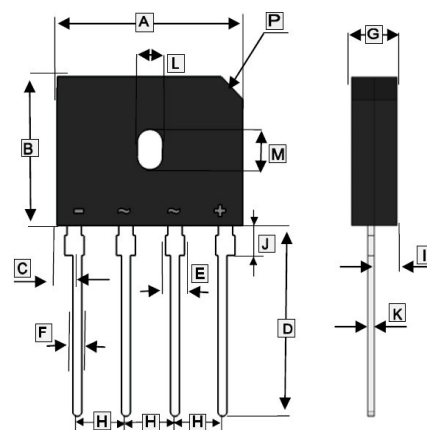
FEATURES

- I_o : 8A
- V_{RRM} : 50~1000V
- Glass passivated chip
- High surge forward current capability

APPLICATIONS

- General purpose 1 phase Bridge rectifier applications

GBU



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	21.7	22.3	H	4.83	5.33
B	18.2	18.8	I	1.8	2.66
C	3°45' TYP.		J	1.8	2.54
D	17.5	18.5	K	0.4	0.6
E	1.8	2.54	L	3.5	4.1
F	0.9	1.27	M	5.7 TYP.	
G	3.3	3.8			

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Rating 25°C ambient temperature unless otherwise specified. Single phase half wave, 60Hz, resistive or inductive load.
For capacitive load, de-rate current by 20%.)

Parameter		Symbol	Part Number							Unit
			GBU 8005	GBU 801	GBU 802	GBU 804	GBU 806	GBU 808	GBU 810	
Maximum Recurrent Peak Reverse Voltage		V _{RRM}	50	100	200	400	600	800	1000	V
Average Rectified Output Current @ 60Hz sine wave, R-load	With heatsink T _C =110℃	I _O	8							A
	Without heatsink T _A =25℃		3.2							
Surge (Nonrepetitive) Forward Current @ 60Hz sine wave, 1 cycle, T _J =25℃		I _{FSM}	150							A
Current Squared Time ¹		I ² t	93							A ² S
Dielectric Strength@ Terminals to case , AC 1 minute		V _{DIS}	2							KV
Mounting Torque@ Recommend torque : 5kg.cm		Tor	8							Kg.cm
Peak Forward Voltage@ I _{FM} =4A, Pulse measurement, Rating of per diode		V _{FM}	1.1							V
Peak Reverse Current@ V _{RM} =V _{RRM} , Pulse measurement, Rating of per diode		I _{RRM}	10							μA
Thermal Resistance	Without heatsink	R _{θJA}	25							℃ / W
	With heatsink	R _{θJC}	2.3							
Junction and Storage temperature range		T _J ,T _{STG}	-55~+150							℃

Notes :

1. $1\text{ms} \leq t < 8.3\text{ms}$ $T_J=25^\circ\text{C}$, Rating of per diode

RATINGS AND CHARACTERISTIC CURVES

FIG1: I_o - T_c Curve

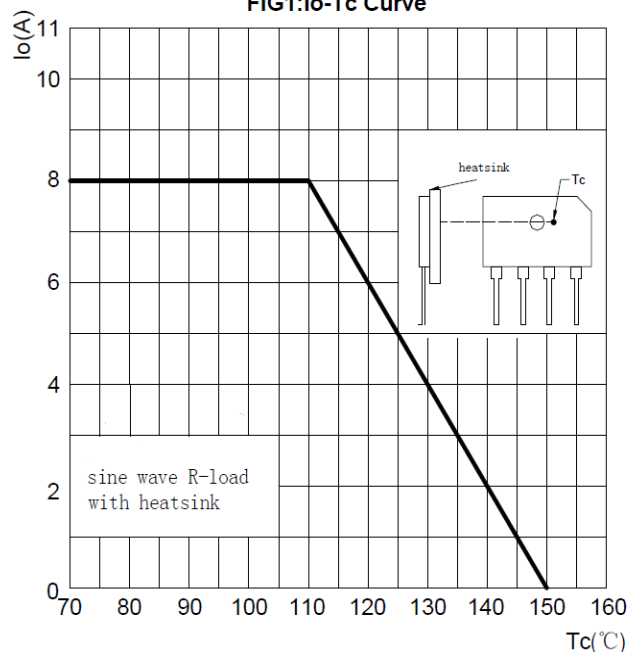


FIG2: Surge Forward Current Capacity

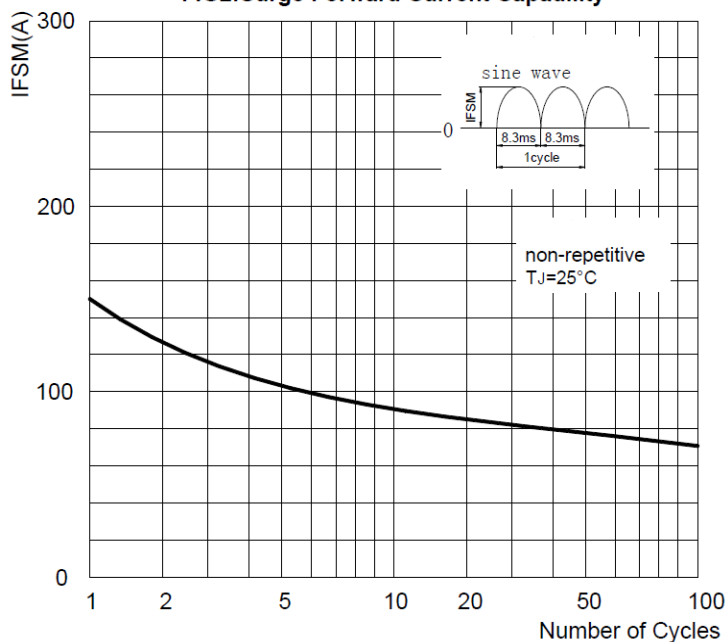


FIG3: Forward Voltage

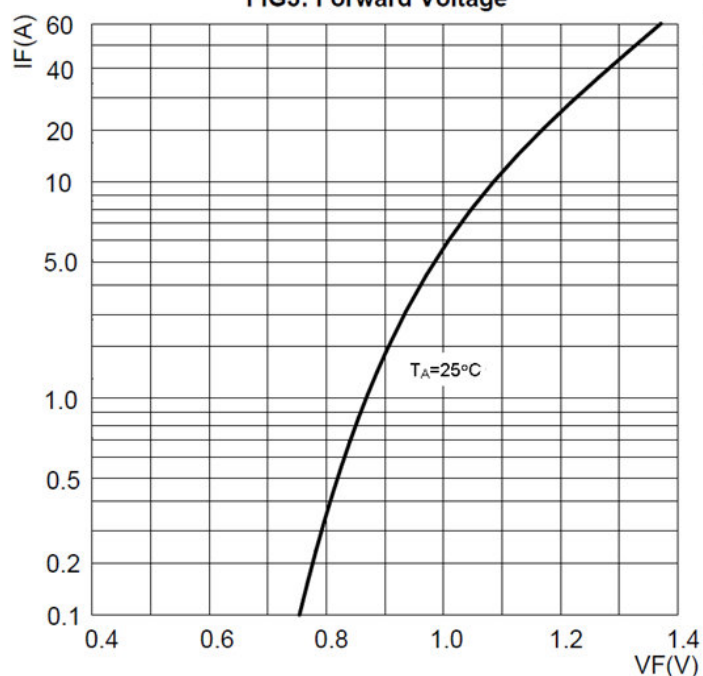


FIG4: Typical Reverse Characteristics

